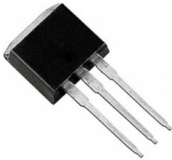




Trench MOS Barrier Schottky Rectifier

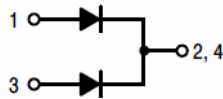
TO-220AB
TSR20L150CT**ITO-220AB**
TSR20L150CTF**TO-262**
TSR20L150CTI**TO-263**
TSR20L150CTB

Features

- Advanced trench technology
- Low forward voltage drop
- Low power losses
- High efficiency operation
- Lead Free Finish, RoHS Compliant

Applications

- DC/DC Converters
- AC/DC Adaptors
- Switching Power Supplies
- Freewheeling Diodes



Maximum ratings and electrical characteristics (T_J = 25°C unless otherwise noted)

Parameter			Symbol	Limit		Unit
Maximum repetitive peak reverse voltage			VRRM	150		V
Maximum average forward rectified current	per device		IF(AV)	20		A
	per diode			10		
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode			IFSM	200		A
Operating junction and storage temperature range			TJ, TSTG	-65 to +150		℃
Typical thermal resistance per leg	TO-220AB/TO-263		RθJC	2		℃/W
	ITO-220AB/TO-262			4		℃/W
Instantaneous forward voltage per diode			VF(1)	TYP.	MAX.	V
	IF=10A	TJ=25℃		-	0.85	
	IF=10A	TJ=125℃		0.68	0.70	
Instantaneous reverse current per diode at rated reverse voltage	TJ=25℃		IR(2)	-	50	uA
	TJ=125℃			-	10	mA

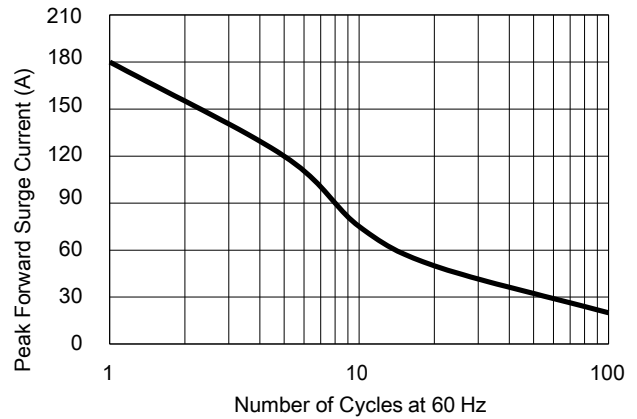
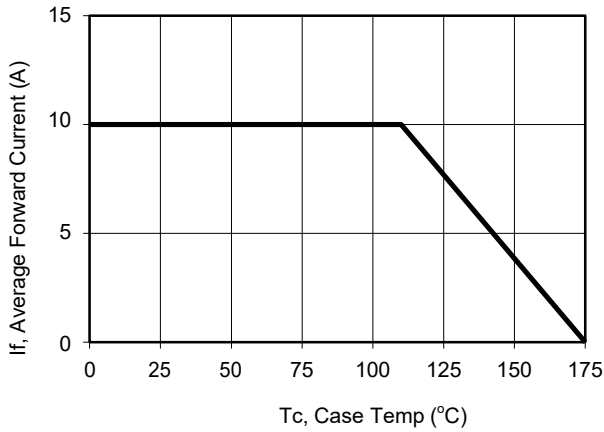
Notes:

(1) Pulse test: 300 μs pulse width, 1 % duty cycle

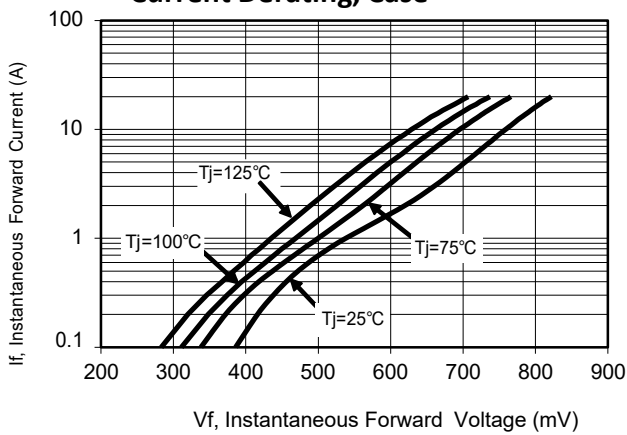
(2) Pulse test: Pulse width ≤ 40 ms

TSR20L150CT\CTF \CTI\CTB Rev 1.0

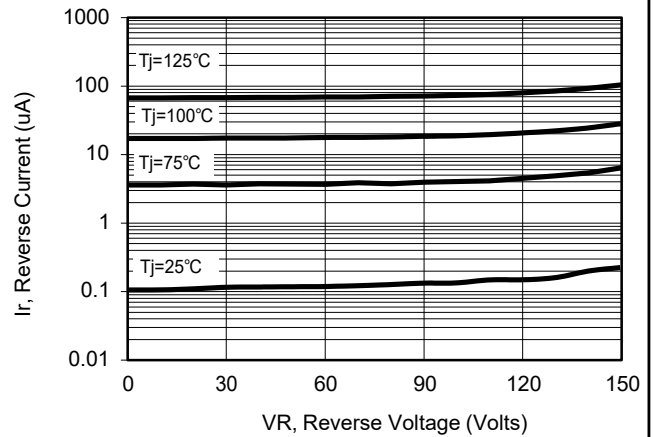
RATINGS AND CHARACTERISTICS CURVES (TA = 25 °C unless otherwise noted)



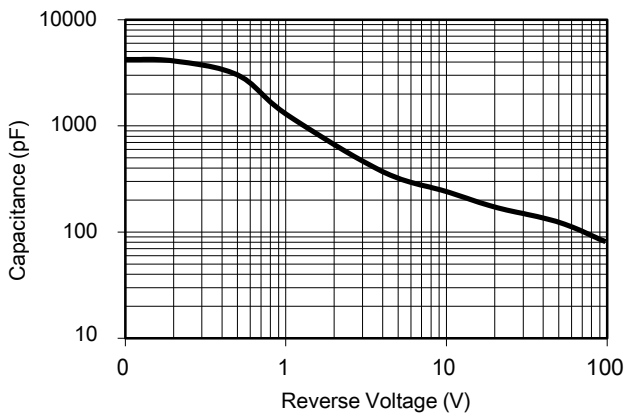
Current Derating, Case



Maximum Repetitive Surge Current



Typical Forward Voltage

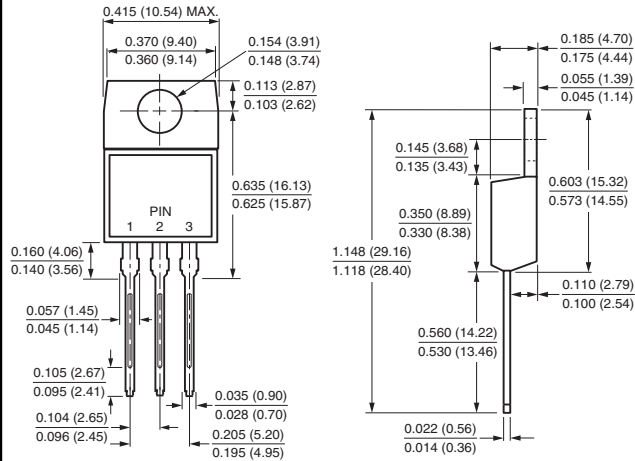


Typical Reverse Current

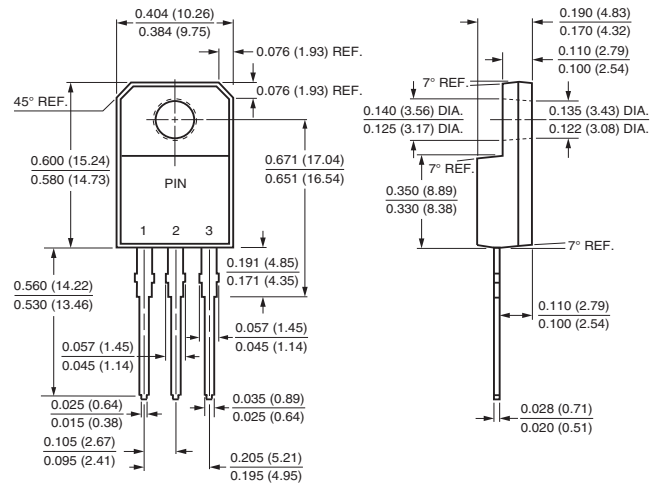
Typical Junction Capacitance

PACKAGE OUTLINE DIMENSIONS

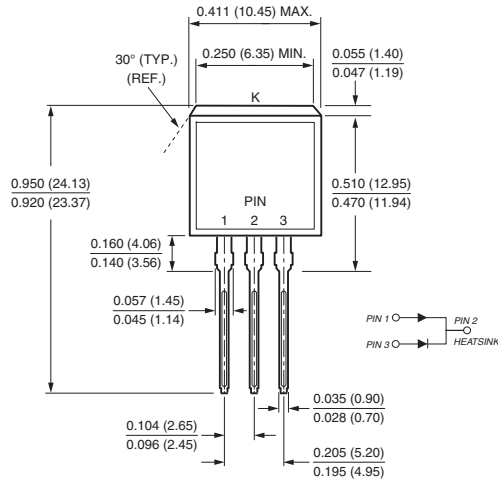
TO-220AB



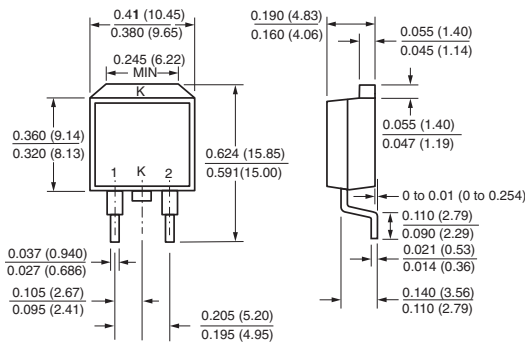
ITO-220AB



TO-262AA



TO-263AB



Mounting Pad Layout

